# **2SD0973A** (2SD973A)

# Silicon NPN epitaxial planar type

## For low-frequency driver amplification

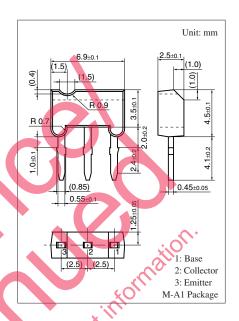
#### ■ Features

- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

## ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	60	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V
Collector current	$I_C$	1	A
Peak collector current	$I_{CP}$	1.5	A
Collector power dissipation *	P <sub>C</sub>	1	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Note) \*: Printed circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion



# ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10  \mu \text{A}, I_{\rm E} = 0$	60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 2 \text{ mA}$ $I_B = 0$	50			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}, I_C \neq 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{ V. Lp} = 0$			0.1	μΑ
Forward current transfer ratio *1	h <sub>FE1</sub> *2	$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$	85		340	_
	h <sub>FE2</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$	50			
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.2	0.4	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.85	1.2	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		20	30	pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

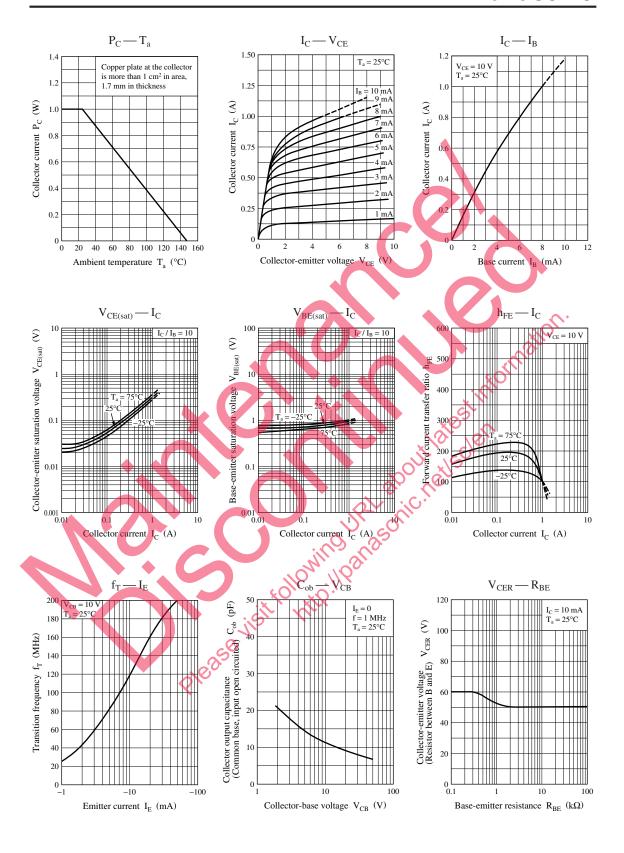
#### 2. \*1: Pulse measurement

#### \*2: Rank classification

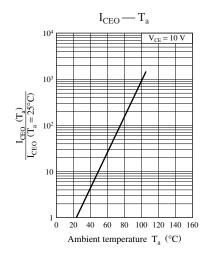
Rank	Q	R	S
$h_{\rm FE1}$	85 to 170	120 to 240	170 to 340

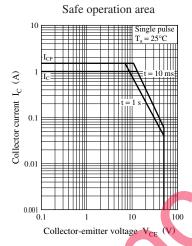
Note) The part number in the parenthesis shows conventional part number.

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